

EMP311

ISSUED DATE: 09-10-04

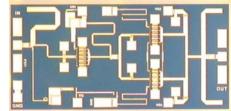
21.0 - 24.0 GHz Power Amplifier MMIC

FEATURES

- 21.0 24.0 GHz Operating Frequency Range
- 26.5dBm Output Power at 1dB Compression
- 14.0 dB Typical Small Signal Gain
- -40dBc OIMD3 @Each Tone Pout 16.5dBm

APPLICATIONS

- Point-to-point and point-to-multipoint radio
- Military Radar Systems



Dimension: 1130um X 2250um Thickness: 75um ± 13um



Caution! ESD sensitive device.

ELECTRICAL CHARACTERISTICS (T_a = 25 °C, 50 ohm, VDD=7V, IDQ=380mA)

SYMBOL	PARAMETER/TEST CONDITIONS	MIN	TYP	MAX	UNITS
F	Operating Frequency Range	21.0		24.0	GHz
P1dB	Output Power at 1dB Gain Compression	25.0	26.5		dBm
Gss	Small Signal Gain	11.0	14.0		dB
OIMD3	Output 3 rd Order Intermodulation Distortion @∆f=10MHz, Each Tone Pout 16.5dBm		-40	-37	dBc
Input RL	Input Return Loss		-10	-8	dB
Output RL	Output Return Loss		-8	-6	dB
ldss	Saturate Drain Current V _{DS} =3V, V _{GS} =0V	429	536	644	mA
V _{DD}	Power Supply Voltage		7	8	V
Rth	Thermal Resistance (Au-Sn Eutectic Attach)		18		°C/W
Tb	Operating Base Plate Temperature	-35		+85	°C

ABSOLUTE MAXIMUM RATINGS FOR CONTINUOUS OPERATION1,2

SYMBOL	CHARACTERISTIC	VALUE	
V_{DS}	Drain to Source Voltage	8 V	
V_{GS}	Gate to Source Voltage	-4 V	
I _{DD}	Drain Current	ldss	
I_{GSF}	Forward Gate Current	7.5mA	
P _{IN}	Input Power	@ 3dB compression	
T_CH	Channel Temperature	150°C	
T _{STG}	Storage Temperature	-65/150°C	
P_T	Total Power Dissipation	6.3W	

^{1.} Operating the device beyond any of the above rating may result in permanent damage.

^{2.} Bias conditions must also satisfy the following equation $V_{DS}*I_{DS} < (T_{CH} - T_{HS})/R_{TH}$; where T_{HS} = ambient temperature



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Chip Thickness: 75±13 microns

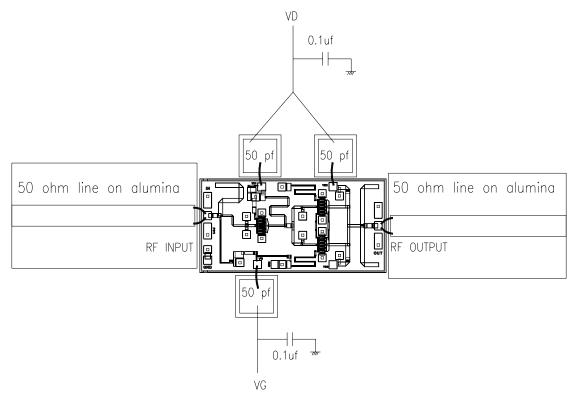
All Dimensions in Microns

PAD Dimensions: 100 x 100 microns

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PRELIMINARY DATA SHEET **ASSEMBLY DRAWING**

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The length of RF wires should be as short as possible. Use at least two wires between RF pad and 50 ohm line and separate the wires to minimize the mutual inductance.

CHIP OUTLINE 1611 1130 RF IN 673 山口 RF DUT 565 GND 6 1610 909 Chip size 1130 X 2250 microns

Specifications are subject to change without notice.

SNB SNB

Excelics Semiconductor, Inc. 310 De Guigne Drive, Sunnyvale, CA 94085 Phone: 408-737-1711 Fax: 408-737-1868 Web: www.excelics.com Revised September 2004

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